

Virginia Boldrini

List of Publications by Year in descending order

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2258059

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citing authors

#	ARTICLE	IF	CITATIONS
1	Analysis of the electrical activation data in thermally annealed implanted Al/4H-SiC systems: A novel approach based on cooperativity. <i>Materials Science in Semiconductor Processing</i> , 2022, 148, 106825.	4.0	2
2	Characterization and modeling of thermally-induced doping contaminants in high-purity germanium. <i>Journal Physics D: Applied Physics</i> , 2019, 52, 035104.	2.8	11
3	Diffusion doping of germanium by sputtered antimony sources. <i>Materials Science in Semiconductor Processing</i> , 2018, 75, 118-123.	4.0	8
4	Optimal process parameters for phosphorus spin-on-doping of germanium. <i>Applied Surface Science</i> , 2017, 392, 1173-1180.	6.1	18
5	$3 \times 10^{18} \text{ cm}^{-3}$ - $1 \times 10^{19} \text{ cm}^{-3}$; Al ⁺ ; Ion Implanted 4H-SiC: Annealing Time Effect. <i>Materials Science Forum</i> , 0, 1004, 683-688.	0.3	4
6	Ion Implanted Phosphorous for 4H-SiC VDMOSFETs Source Regions: Effect of the Post Implantation Annealing Time. <i>Materials Science Forum</i> , 0, 1004, 698-704.	0.3	1
7	Estimation of Activation and Compensation Ratios in Al ⁺ ; Ion Implanted 4H-SiC: Comparison of Two Methodologies. <i>Materials Science Forum</i> , 0, 1062, 241-245.	0.3	1